

STP42N60M2-EP-VB Datasheet

N-Channel 600V (D-S) Super Junction Power MOSFET

| PRODUCT SUMMARY | | |
|------------------------------------|-----------------|-------|
| V_{DS} (V) at T_J max. | 600 | |
| $R_{DS(on)}$ at 25 °C (Ω) | $V_{GS} = 10$ V | 0.085 |

FEATURES

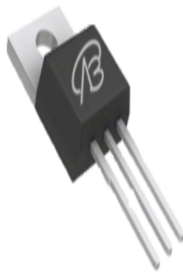
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



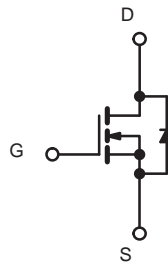
APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial

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Top View



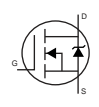
N-Channel MOSFET

| ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted) | | | | |
|---|------------------|----------------|-------------|------|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | V_{DS} | 600 | V | |
| Gate-Source Voltage | V_{GS} | ± 30 | | |
| Continuous Drain Current ($T_J = 150$ °C) | V_{GS} at 10 V | $T_C = 25$ °C | 32 | A |
| | | $T_C = 100$ °C | 20 | |
| Pulsed Drain Current ^a | | I_{DM} | 96 | |
| Linear Derating Factor | | | 1.67 | W/°C |
| Single Pulse Avalanche Energy ^b | | E_{AS} | 1300 | mJ |
| Maximum Power Dissipation | | P_D | 230 | W |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | -55 to +150 | °C |
| Drain-Source Voltage Slope | $T_J = 125$ °C | dV/dt | 50 | V/ns |
| Reverse Diode dV/dt ^d | | | 15 | |
| Soldering Recommendations (Peak Temperature) ^c | for 10 s | | 260 | °C |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 100$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_G = 25$ Ω , $I_{AS} = 16$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

| THERMAL RESISTANCE RATINGS | | | | |
|----------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 62 | °C/W |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 0.7 | |

| SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted) | | | | | | | |
|---|---------------------|---|---|--|-------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$ | | 600 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$ | | - | 0.70 | - | V/°C |
| Gate-Source Threshold Voltage (N) | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2.5 | - | 4.5 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| | | $V_{GS} = \pm 30\text{ V}$ | | - | - | ± 1 | μA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 1 | μA |
| | | $V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | 100 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 10.5\text{ A}$ | - | 0.085 | - | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 30\text{ V}, I_D = 10.5\text{ A}$ | | - | 5.6 | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$ | | - | 3500 | - | pF |
| Output Capacitance | C_{oss} | | | - | 80 | - | |
| Reverse Transfer Capacitance | C_{rss} | | | - | 4 | - | |
| Effective Output Capacitance, Energy Related ^a | $C_{o(er)}$ | $V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$ | | - | 62 | - | |
| Effective Output Capacitance, Time Related ^b | $C_{o(tr)}$ | | | - | 213 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 8\text{ A}, V_{DS} = 520\text{ V}$ | - | 5.7 | - | nC |
| Gate-Source Charge | Q_{gs} | | | - | 15 | - | |
| Gate-Drain Charge | Q_{gd} | | | - | 1.9 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 520\text{ V}, I_D = 8\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$ | | - | 18 | 25 | ns |
| Rise Time | t_r | | | - | 24 | 55 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 8.0 | - | |
| Fall Time | t_f | | | - | 1.2 | - | |
| Gate Input Resistance | R_g | | | $f = 1\text{ MHz}, \text{ open drain}$ | | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode  | | - | - | 32 | A |
| Pulsed Diode Forward Current | I_{SM} | | | - | - | 96 | |
| Diode Forward Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 8\text{ A}, V_{GS} = 0\text{ V}$ | | - | - | 1.5 | V |
| Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$ | | - | 475 | - | ns |
| Reverse Recovery Charge | Q_{rr} | | | - | 5.8 | - | μC |
| Reverse Recovery Current | I_{RRM} | | | - | 35 | - | A |

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Fig. 1 - Typical Output Characteristics



Fig. 4 - Normalized On-Resistance vs. Temperature



Fig. 2 - Typical Output Characteristics



Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

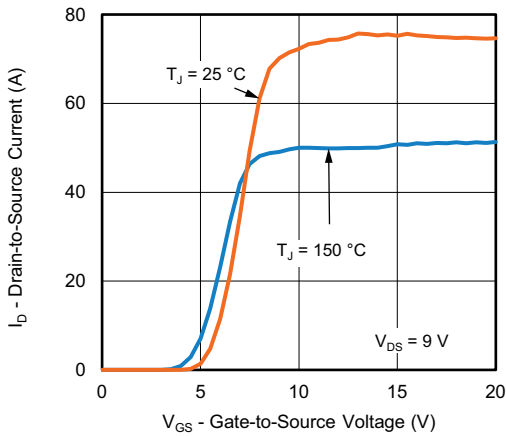


Fig. 3 - Typical Transfer Characteristics

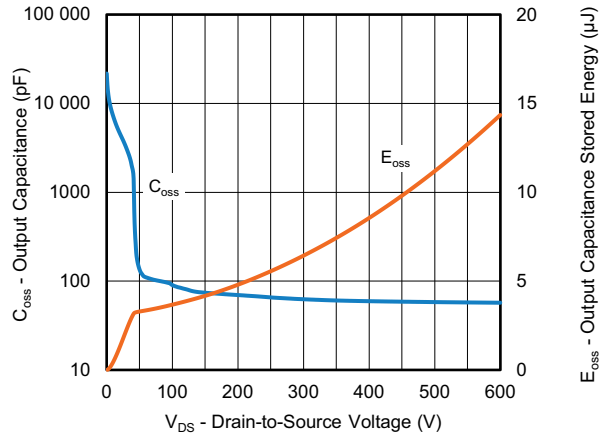


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

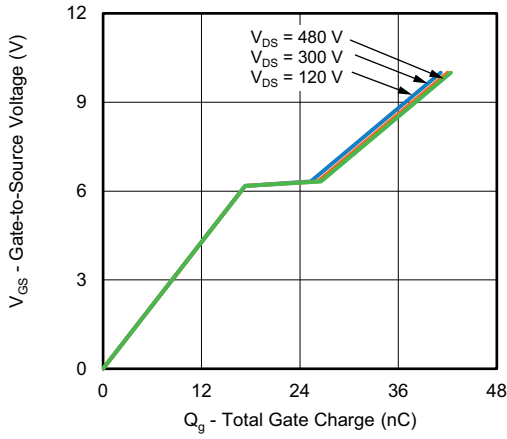


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 10 - Maximum Drain Current vs. Case Temperature

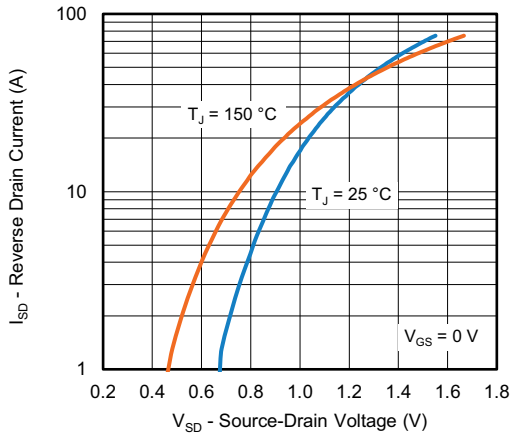


Fig. 8 - Typical Source-Drain Diode Forward Voltage

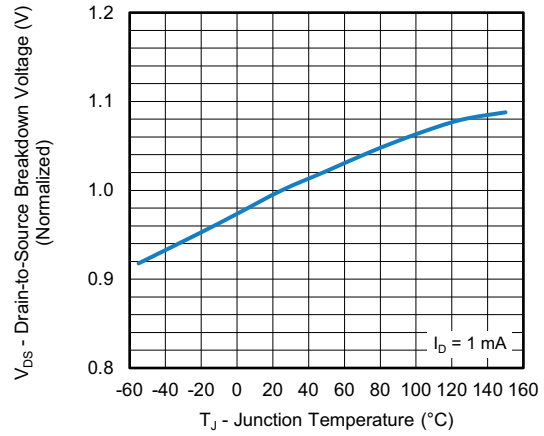


Fig. 11 - Temperature vs. Drain-to-Source Voltage



Fig. 9 - Maximum Safe Operating Area

Note

a. $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

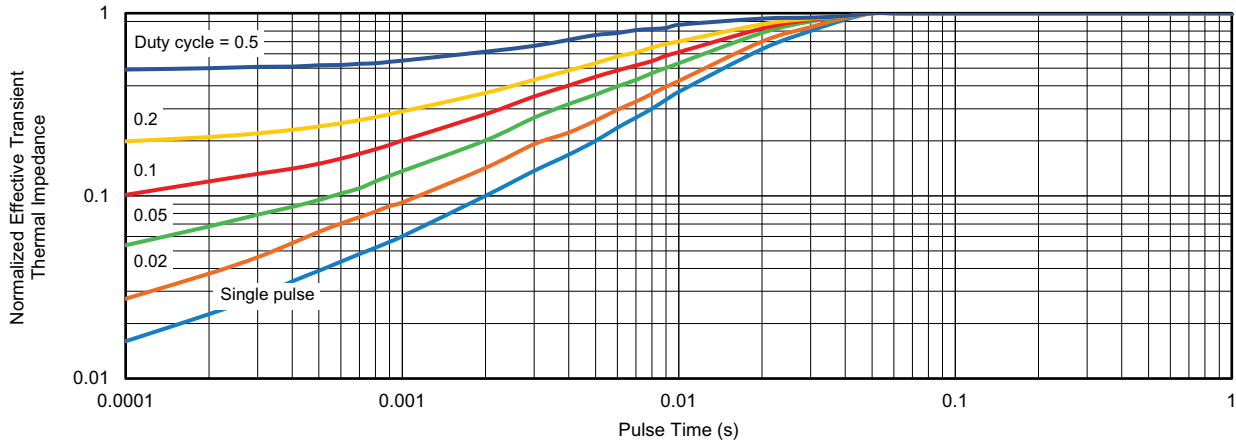


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case



Fig. 13 - Switching Time Test Circuit

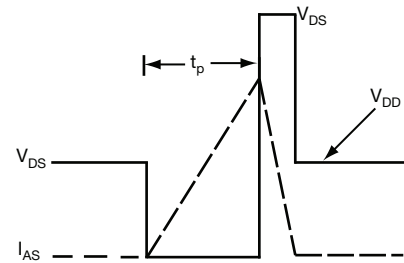


Fig. 16 - Unclamped Inductive Waveforms



Fig. 14 - Switching Time Waveforms



Fig. 17 - Basic Gate Charge Waveform

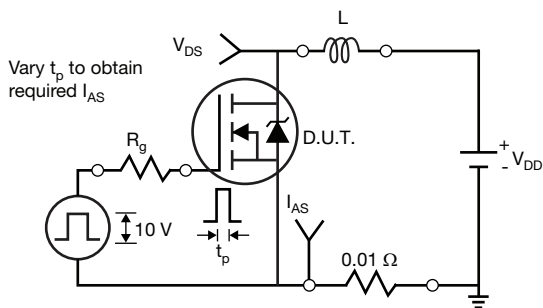
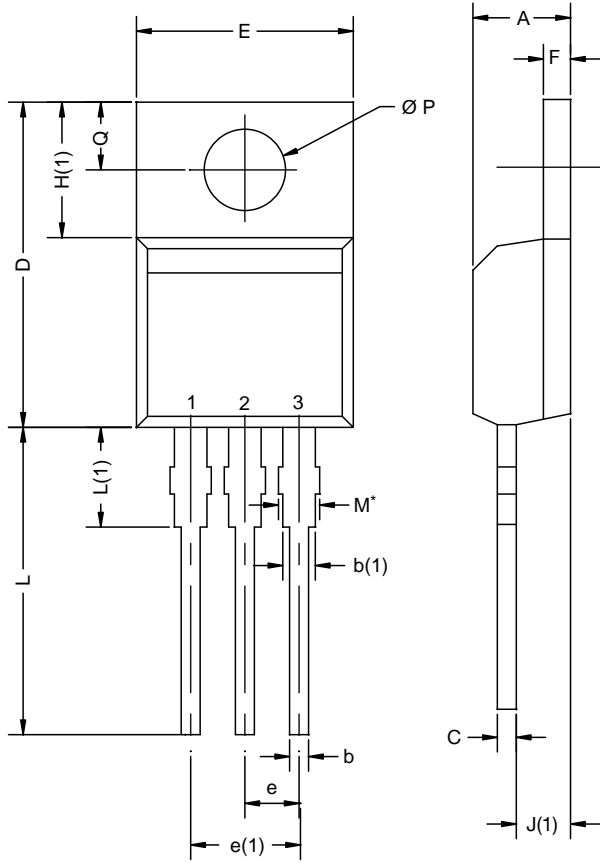


Fig. 15 - Unclamped Inductive Test Circuit



Fig. 18 - Gate Charge Test Circuit

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| DIM. | MILLIMETERS | | INCHES | |
|-----------------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.25 | 4.65 | 0.167 | 0.183 |
| b | 0.69 | 1.01 | 0.027 | 0.040 |
| b(1) | 1.20 | 1.73 | 0.047 | 0.068 |
| c | 0.36 | 0.61 | 0.014 | 0.024 |
| D | 14.85 | 15.49 | 0.585 | 0.610 |
| E | 10.04 | 10.51 | 0.395 | 0.414 |
| e | 2.41 | 2.67 | 0.095 | 0.105 |
| e(1) | 4.88 | 5.28 | 0.192 | 0.208 |
| F | 1.14 | 1.40 | 0.045 | 0.055 |
| H(1) | 6.09 | 6.48 | 0.240 | 0.255 |
| J(1) | 2.41 | 2.92 | 0.095 | 0.115 |
| L | 13.35 | 14.02 | 0.526 | 0.552 |
| L(1) | 3.32 | 3.82 | 0.131 | 0.150 |
| $\varnothing P$ | 3.54 | 3.94 | 0.139 | 0.155 |
| Q | 2.60 | 3.00 | 0.102 | 0.118 |

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DWG: 5471

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
Heatsink hole for HVM

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